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## United States Patent and Trademark Office

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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
09/371,955	08/11/1999	SHANE P. LEIPHART	M4065.0196/P 9847		
7	590 01/02/2002				
THOMAS J D AMICO ESQ DICKSTEIN SHAPIRO MORIN & OSHINSKY LLP 2101 L STREET NW			EXAMINER		
			KANG, DONGHEE		
WASHINGTO	N, DC 200371526		ART UNIT	PAPER NUMBER	
			2811		
			DATE MAILED: 01/02/2002		

Please find below and/or attached an Office communication concerning this application or proceeding.

					<u></u>			
		Application	on No.	Applicant(s)				
	•	09/371,95	5	LEIPHART, SHANE P.				
Office Action Summary		Examin r		Art Unit				
		Donghee		2811				
The MAILING DATE of this communication appears on the cover sheet with the correspondence address Period for Reply								
THE N - Exten after: - If the - If NO - Failur - Any r	DRTENED STATUTORY PERIOD FOR REMAILING DATE OF THIS COMMUNICATION Sions of time may be available under the provisions of 37 CF SIX (6) MONTHS from the mailing date of this communication period for reply specified above is less than thirty (30) days, a period for reply is specified above, the maximum statutory per to reply within the set or extended period for reply will, by supply received by the Office later than three months after the modern patent term adjustment. See 37 CFR 1.704(b).	DN. R 1.136(a). In no even. r. a reply within the statueriod will apply and will tatute. cause the apply.	ent, however, may a reply be til utory minimum of thirty (30) day Il expire SIX (6) MONTHS from ication to become ABANDONE	mely filed  ys will be considered timely.  n the mailing date of this communicati ED (35 U.S.C. § 133).	ion.			
1)	Responsive to communication(s) filed on	18 September	2001 .					
2a)□	•	This action is						
3)								
Dispositi	on of Claims							
4) Claim(s) <u>26-40</u> is/are pending in the application.								
4a) Of the above claim(s) is/are withdrawn from consideration.								
5)[	Claim(s) is/are allowed.							
6)⊠	Claim(s) <u>26-40</u> is/are rejected.							
7)	Claim(s) is/are objected to.							
8) Claim(s) are subject to restriction and/or election requirement.								
Application Papers								
9) The specification is objected to by the Examiner.								
10) The drawing(s) filed on is/are: a) accepted or b) objected to by the Examiner.								
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).								
11) ☐ The proposed drawing correction filed on is: a) ☐ approved b) ☐ disapproved by the Examiner.								
If approved, corrected drawings are required in reply to this Office action.								
12) The oath or declaration is objected to by the Examiner.								
Priority u	inder 35 U.S.C. §§ 119 and 120							
13) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).								
a) All b) Some * c) None of:								
	1. Certified copies of the priority documents have been received.							
	2. Certified copies of the priority documents have been received in Application No							
3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)). * See the attached detailed Office action for a list of the certified copies not received.								
14) Acknowledgment is made of a claim for domestic priority under 35 U.S.C. § 119(e) (to a provisional application).								
a) The translation of the foreign language provisional application has been received.  15) Acknowledgment is made of a claim for domestic priority under 35 U.S.C. §§ 120 and/or 121.								
Attachmen								
1)  Notic	e of References Cited (PTO-892) e of Draftsperson's Patent Drawing Review (PTO-948 nation Disclosure Statement(s) (PTO-1449) Paper No			ry (PTO-413) Paper No(s) Patent Application (PTO-152)	<b></b> .			

U.S. Patent and Trademark Office PTO-326 (Rev. 04-01) Art Unit: 2811

#### **DETAILED ACTION**

## **Continued Prosecution Application**

1. The request filed on September 18, 2001 for a Continued Prosecution

Application (CPA) under 37 CFR 1.53(d) based on parent Application No. 09/371,955 is

acceptable and a CPA has been established. An action on the CPA follows.

# Claim Rejections - 35 USC § 103

- 2. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
  - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 3. Claims **26-32 & 37-40** are rejected under 35 U.S.C. 103(a) as being unpatentable over Harada et al (US 5,313,101) in view of Kanamori (US 5,281,850).

Regarding claims **26-32**, Harada et al discloses a semiconductor device comprising (Fig.2G):

a memory circuit region in a semiconductor substrate; a first dielectric layer (3); an aluminum layer (4) over the dielectric layer; a contact interconnect between the aluminum layer (4) and substrate (1); a second dielectric layer (5) on the aluminum layer; a via hole extending through the second dielectric layer to aluminum layer; a titanium aluminide layer (206) lining at least a bottom of the via hole; a titanium compound layer (102) formed on the titanium aluminide; a conductive material (103') formed on the titanium nitride layer; and a second metallic layer (103) on the second

dielectric layer and electrically connected to the plug material. Harada does not teach a preformed titanium aluminide. The term "preformed" is process

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limitation which recites process step to form the structure claimed in 26-28. The process limitation is given no patentable weight in device claim. The final structure of claimed invention is identical to the Harada's device. Therefore, claimed structure is taken to be in the least obvious over Ichikawa.

If the product in the product-by-process claim is the same as or obvious from a product of the prior art, the claim is unpatentable even though the prior the prior product was made by a different process". In re Thorpe, 777F. 2d 695,698 USPQ 964, 966 (Fed. Cir. 1985). See also MPEP 2113. Moreover, an old or obvious product produced by a new method is not a patentable product, whether claim in "product by process" claim or not.

Harada et al does not teach an antireflecting coating layer over the aluminum layer.

However, Kanamori teaches in Fig.1(f) the antireflecting coating layer (5) located at between aluminum layer and second dielectric layer. It is common to use a layer of material to suppress reflections from underlying surfaces during photolithography exposure steps. Therefore, it would have been obvious to one having ordinary skill in the art at the time the invention was made to form the antireflecting coating layer, since antireflecting coating layer suppresses reflections from underlying layers so that the photoresist is not exposed to the reflected light wave, which leads to variation in critical dimensions.

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Regarding claims **37-40**, Harada et al discloses a semiconductor device comprising (Fig.2G):

a memory circuit region in a semiconductor substrate; a first dielectric layer (3) over the memory circuit region; a first metallic layer (4) over the first dielectric layer; a contact interconnect between the first metallic layer (4) and the substrate (1); a second dielectric layer (5) on the first metallic (aluminum) layer; a via hole extending through the second dielectric layer to a surface of the second metallic layer; a titanium aluminide layer (206) lining at least a bottom of the via hole; a titanium compound layer (102) formed on the titanium aluminide; a conductive material (103') formed on the titanium compound layer; and a second metallic layer (103) on the second dielectric layer and electrically connected to the plug material.

Harada et al does not teach an antireflecting coating over the aluminum layer.

However, Kanamori teaches in Fig.1(f) the antireflecting coating layer (5) located at between aluminum layer and second dielectric layer. It is common to use a layer of material to suppress reflections from underlying surfaces during photolithography exposure steps. Therefore, it would have been obvious to one having ordinary skill in the art at the time the invention was made to form the antireflecting coating layer, since antireflecting coating layer suppresses reflections from underlying layers so that the photoresist is not exposed to the reflected light wave, which leads to variation in critical dimensions.

Neither Harada et al nor Kanamori teaches a computer system in which comprises a semiconductor device as teaching by Harada et al as modified by

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Kanamori. It would have been obvious to one of ordinary skill in the art to have a processor in computer system since a RAM fabricated on a semiconductor chip communicates with the processor while computer is operating.

4. Claims **33-36** are rejected under 35 U.S.C. 103(a) as being unpatentable over Harada et al in view of Kanamori, as applied claim **28** above, and further in view of Clayton (US 4,656,605).

Regarding claims **33-36**, Harada et al as modified by Kanamori teaches all claimed structure as claimed in claims 33-40, as explained above in claim 28.

Neither Harada nor Kanamori teaches preformed titanium aluminide layer being volume reduced. However, the term "preformed titanium aluminide layer being volume reduced" is process limitation which recites process step to form the structure claimed in 33-36. The process limitations are given no patentable weight in device claim. The final structure of claimed invention is identical to the Harada's device. Therefore, claimed structure is taken to be in the least obvious over Harada.

Neither Harada nor Kanamori teaches a memory module which include a semiconductor device. However, Clayton teaches the memory module comprising (Fig.2):

a substrate comprising a circuit board (31); a plurality of memory chips (10-18) mounted on the substrate and connected to form a memory circuit, wherein one or more of the memory chips comprises a random access memory (RAM) fabricated on a

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semiconductor substrate which comprising the teaching of Harada; and an edge connector (20) along one edge of the substrate which is wired to said memory circuit. It would have been obvious to one of ordinary skill in the art at the time the invention was made to have module system, since module system includes a plurality of components each storing or reading on binary bit at a time in the semiconductor memory device.

## Conclusion

5. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Donghee Kang whose telephone number is 703-305-9147. The examiner can normally be reached on Monday through Friday.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Tom Thomas can be reached on 703-308-2772. The fax phone numbers for the organization where this application or proceeding is assigned are 703-308-7722 for regular communications and 703-308-7722 for After Final communications.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is 703-308-0956.

Donghee Kang, Ph.D. December 21, 2001

TOM THOMAS SUPERVISORY PATENT EXAMINER **TECHNOLOGY CENTER 2800**